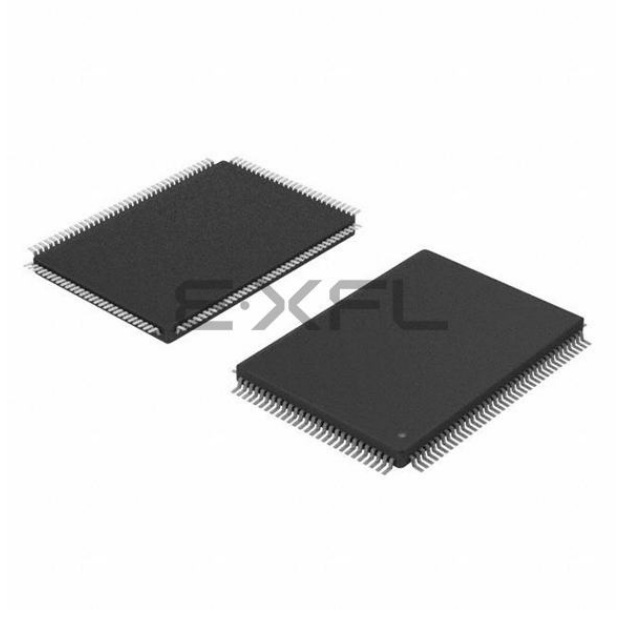

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	M16C/60
Core Size	16-Bit
Speed	24MHz
Connectivity	I²C, IEBus, UART/USART
Peripherals	DMA, WDT
Number of I/O	113
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 26x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	128-LQFP
Supplier Device Package	128-LFQFP (14x20)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/m30625fgpgp-u9c

1.2 Performance Outline

Table 1.1 to 1.3 list Performance Outline of M16C/62P Group (M16C/62P, M16C/62PT)(128-pin version).

Table 1.1 Performance Outline of M16C/62P Group (M16C/62P, M16C/62PT)(128-pin version)

	Item	Performance
		M16C/62P
CPU	Number of Basic Instructions	91 instructions
	Minimum Instruction Execution Time	41.7ns(f(BCLK)=24MHz, VCC1=3.3 to 5.5V) 100ns(f(BCLK)=10MHz, VCC1=2.7 to 5.5V)
	Operating Mode	Single-chip, memory expansion and microprocessor mode
	Address Space	1 Mbyte (Available to 4 Mbytes by memory space expansion function)
	Memory Capacity	See **Table 1.4 to 1.5 Product List**
Peripheral Function	Port	Input/Output : 113 pins, Input : 1 pin
	Multifunction Timer	Timer A : 16 bits x 5 channels, Timer B : 16 bits x 6 channels, Three phase motor control circuit
	Serial Interface	3 channels Clock synchronous, UART, I2C bus(1), IEBus(2) 2 channels Clock synchronous
	A/D Converter	10-bit A/D converter: 1 circuit, 26 channels
	D/A Converter	8 bits x 2 channels
	DMAC	2 channels
	CRC Calculation Circuit	CCITT-CRC
	Watchdog Timer	15 bits x 1 channel (with prescaler)
	Interrupt	Internal: 29 sources, External: 8 sources, Software: 4 sources, Priority level: 7 levels
	Clock Generation Circuit	4 circuits Main clock generation circuit (*), Subclock generation circuit (*), On-chip oscillator, PLL synthesizer (*)Equipped with a built-in feedback resistor.
	Oscillation Stop Detection Function	Stop detection of main clock oscillation, re-oscillation detection function
	Voltage Detection Circuit	Available (option(4))
Electric Characteristics	Supply Voltage	VCC1=3.0 to 5.5 V, VCC2=2.7V to VCC1 (f(BCLK=24MHz) VCC1=2.7 to 5.5 V, VCC2=2.7V to VCC1 (f(BCLK=10MHz)
	Power Consumption	14 mA (VCC1=VCC2=5V, f(BCLK)=24MHz) 8 mA (VCC1=VCC2=3V, f(BCLK)=10MHz) 1.8μA (VCC1=VCC2=3V, f(XCIN)=32kHz, wait mode) 0.7μA (VCC1=VCC2=3V, stop mode)
Flash memory version	Program/Erase Supply Voltage	3.3±0.3 V or 5.0±0.5 V
	Program and Erase Endurance	100 times (all area) or 1,000 times (user ROM area without block A and block 1) / 10,000 times (block A, block 1) (3)
Operating Ambient Temperature		-20 to 85°C, -40 to 85°C (3)
Package		128-pin plastic mold LQFP

NOTES:
1. I2C bus is a registered trademark of Koninklijke Philips Electronics N. V.
2. IEBus is a registered trademark of NEC Electronics Corporation.
3. See **Table 1.8 Product Code** for the program and erase endurance, and operating ambient temperature. In addition 1,000 times/10,000 times are under development as of Jul., 2005. Please inquire about a release schedule.
4. All options are on request basis.

Table 1.9 Product Code of Flash Memory version for M16C/62PT

		Product Code	Package	Internal ROM (User ROM Area Without Block A, Block 1)		Internal ROM (Block A, Block 1)		Operating Ambient Temperature
				Program and Erase Endurance	Temperature Range	Program and Erase Endurance	Temperature Range	
Flash memory Version	T Version	B	Lead-included	100	0°C to 60°C	100	0°C to 60°C	-40°C to 85°C
	V Version							-40°C to 125°C
	T Version	B7		1,000		10,000	-40°C to 85°C	-40°C to 85°C
	V Version						-40°C to 125°C	-40°C to 125°C
	T Version	U	Lead-free	100		100	0°C to 60°C	-40°C to 85°C
	V Version							-40°C to 125°C
	T Version	U7		1,000		10,000	-40°C to 85°C	-40°C to 85°C
	V Version						-40°C to 125°C	-40°C to 125°C

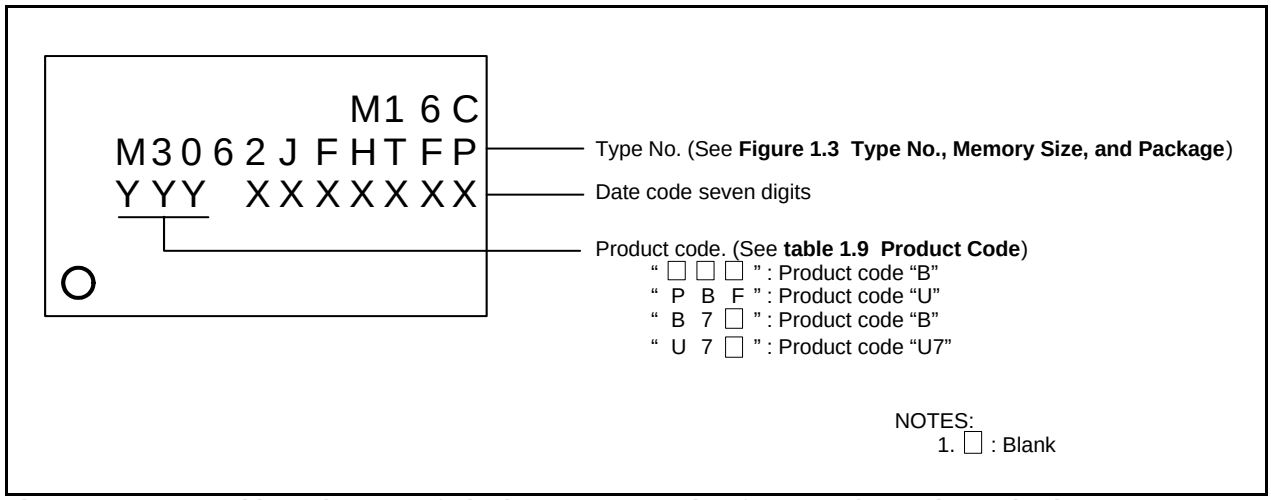


Figure 1.5 Marking Diagram of Flash Memory version for M16C/62PT (Top View)

Table 1.16 Pin Characteristics for 80-Pin Package (2)

Pin No.	Control Pin	Port	Interrupt Pin	Timer Pin	UART Pin	Analog Pin	Bus Control Pin
51		P3_0					
52		P2_7				AN2_7	
53		P2_6				AN2_6	
54		P2_5				AN2_5	
55		P2_4				AN2_4	
56		P2_3				AN2_3	
57		P2_2				AN2_2	
58		P2_1				AN2_1	
59		P2_0				AN2_0	
60		P0_7				AN0_7	
61		P0_6				AN0_6	
62		P0_5				AN0_5	
63		P0_4				AN0_4	
64		P0_3				AN0_3	
65		P0_2				AN0_2	
66		P0_1				AN0_1	
67		P0_0				AN0_0	
68		P10_7	$\overline{KI3}$			AN7	
69		P10_6	$\overline{KI2}$			AN6	
70		P10_5	$\overline{KI1}$			AN5	
71		P10_4	$\overline{KI0}$			AN4	
72		P10_3				AN3	
73		P10_2				AN2	
74		P10_1				AN1	
75	AVSS						
76		P10_0				AN0	
77	VREF						
78	AVCC						
79		P9_7			SIN4	$\overline{ADTRG}$	
80		P9_6			SOUT4	ANEX1	

Table 1.18 Pin Description (100-pin and 128-pin Version) (2)

Signal Name	Pin Name	I/O Type	Power Supply(1)	Description
Main clock input	XIN	I	VCC1	I/O pins for the main clock generation circuit. Connect a ceramic resonator or crystal oscillator between XIN and XOUT (3). To use the external clock, input the clock from XIN and leave XOUT open.
Main clock output	XOUT	O	VCC1	
Sub clock input	XCIN	I	VCC1	I/O pins for a sub clock oscillation circuit. Connect a crystal oscillator between XCIN and XCOUT (3). To use the external clock, input the clock from XCIN and leave XCOUT open.
Sub clock output	XCOUT	O	VCC1	
BCLK output (2)	BCLK	O	VCC2	Outputs the BCLK signal.
Clock output	CLKOUT	O	VCC2	The clock of the same cycle as fC, f8, or f32 is outputted.
$\overline{\text{INT}}$ interrupt input	$\overline{\text{INT0}}$ to $\overline{\text{INT2}}$	I	VCC1	Input pins for the $\overline{\text{INT}}$ interrupt.
	$\overline{\text{NT3}}$ to $\overline{\text{INT5}}$	I	VCC2	
$\overline{\text{NMI}}$ interrupt input	$\overline{\text{NMI}}$	I	VCC1	Input pin for the $\overline{\text{NMI}}$ interrupt. Pin states can be read by the P8_5 bit in the P8 register.
Key input interrupt input	$\overline{\text{KI0}}$ to $\overline{\text{KI3}}$	I	VCC1	Input pins for the key input interrupt.
Timer A	TA0OUT to TA4OUT	I/O	VCC1	These are timer A0 to timer A4 I/O pins. (however, output of TA0OUT for the N-channel open drain output.)
	TA0IN to TA4IN	I	VCC1	These are timer A0 to timer A4 input pins.
	ZP	I	VCC1	Input pin for the Z-phase.
Timer B	TB0IN to TB5IN	I	VCC1	These are timer B0 to timer B5 input pins.
Three-phase motor control output	U, $\overline{\text{U}}$, V, $\overline{\text{V}}$, W, $\overline{\text{W}}$	O	VCC1	These are Three-phase motor control output pins.
Serial interface	$\overline{\text{CTS0}}$ to $\overline{\text{CTS2}}$	I	VCC1	These are send control input pins.
	$\overline{\text{RTS0}}$ to $\overline{\text{RTS2}}$	O	VCC1	These are receive control output pins.
	CLK0 to CLK4	I/O	VCC1	These are transfer clock I/O pins.
	RXD0 to RXD2	I	VCC1	These are serial data input pins.
	SIN3, SIN4	I	VCC1	These are serial data input pins.
	TXD0 to TXD2	O	VCC1	These are serial data output pins. (however, output of TXD2 for the N-channel open drain output.)
	SOUT3, SOUT4	O	VCC1	These are serial data output pins.
	CLKS1	O	VCC1	This is output pin for transfer clock output from multiple pins function.
I^2C mode	SDA0 to SDA2	I/O	VCC1	These are serial data I/O pins. (however, output of SDA2 for the N-channel open drain output.)
	SCL0 to SCL2	I/O	VCC1	These are transfer clock I/O pins. (however, output of SCL2 for the N-channel open drain output.)

I : Input O : Output I/O : Input and output

NOTES:
1. When use VCC1 > VCC2, contacts due to some points or restrictions to be checked.
2. This pin function in M16C/62PT cannot be used.
3. Ask the oscillator maker the oscillation characteristic.

Table 4.5 SFR Information (5) (1)

Address	Register	Symbol	After Reset
0380h	Count Start Flag	TABSR	00h
0381h	Clock Prescaler Reset Fag	CPSRF	0XXXXXXXb
0382h	One-Shot Start Flag	ONSF	00h
0383h	Trigger Select Register	TRGSR	00h
0384h	Up-Down Flag	UDF	00h (2)
0385h			
0386h	Timer A0 Register	TA0	XXh
0387h			XXh
0388h	Timer A1 Register	TA1	XXh
0389h			XXh
038Ah	Timer A2 Register	TA2	XXh
038Bh			XXh
038Ch	Timer A3 Register	TA3	XXh
038Dh			XXh
038Eh	Timer A4 Register	TA4	XXh
038Fh			XXh
0390h	Timer B0 Register	TB0	XXh
0391h			XXh
0392h	Timer B1 Register	TB1	XXh
0393h			XXh
0394h	Timer B2 Register	TB2	XXh
0395h			XXh
0396h	Timer A0 Mode Register	TA0MR	00h
0397h	Timer A1 Mode Register	TA1MR	00h
0398h	Timer A2 Mode Register	TA2MR	00h
0399h	Timer A3 Mode Register	TA3MR	00h
039Ah	Timer A4 Mode Register	TA4MR	00h
039Bh	Timer B0 Mode Register	TB0MR	00XX0000b
039Ch	Timer B1 Mode Register	TB1MR	00XX0000b
039Dh	Timer B2 Mode Register	TB2MR	00XX0000b
039Eh	Timer B2 Special Mode Register	TB2SC	XXXXXX00b
039Fh			
03A0h	UART0 Transmit/Receive Mode Register	U0MR	00h
03A1h	UART0 Bit Rate Generator	U0BRG	XXh
03A2h	UART0 Transmit Buffer Register	U0TB	XXh
03A3h			XXh
03A4h	UART0 Transmit/Receive Control Register 0	U0C0	00001000b
03A5h	UART0 Transmit/Receive Control Register 1	U0C1	00XX0010b
03A6h	UART0 Receive Buffer Register	U0RB	XXh
03A7h			XXh
03A8h	UART1 Transmit/Receive Mode Register	U1MR	00h
03A9h	UART1 Bit Rate Generator	U1BRG	XXh
03AAh	UART1 Transmit Buffer Register	U1TB	XXh
03ABh			XXh
03ACh	UART1 Transmit/Receive Control Register 0	U1C0	00001000b
03ADh	UART1 Transmit/Receive Control Register 1	U1C1	00XX0010b
03AEh	UART1 Receive Buffer Register	U1RB	XXh
03AFh			XXh
03B0h	UART Transmit/Receive Control Register 2	UCON	X0000000b
03B1h			
03B2h			
03B3h			
03B4h			
03B5h			
03B6h			
03B7h			
03B8h	DMA0 Request Factor Select Register	DM0SL	00h
03B9h			
03BAh	DMA1 Request Factor Select Register	DM1SL	00h
03BBh			
03BCh	CRC Data Register	CRCD	XXh
03BDh			XXh
03BEh	CRC Input Register	CRCIN	XXh
03BFh			

NOTES:
1. The blank areas are reserved and cannot be accessed by users.
2. Bit 5 in the Up-down flag is “0” by reset. However, The values in these bits when read are indeterminate.

X : Nothing is mapped to this bit

5. Electrical Characteristics

5.1 Electrical Characteristics (M16C/62P)

Table 5.1 Absolute Maximum Ratings

Symbol	Parameter		Condition	Rated Value	Unit
V_{CC1}, V_{CC2}	Supply Voltage		V_{CC1}=AVcc	–0.3 to 6.5	V
V_{CC2}	Supply Voltage		V_{CC2}	–0.3 to V_{CC1}+0.1	V
AVcc	Analog Supply Voltage		V_{CC1}=AVcc	–0.3 to 6.5	V
V_I	Input Voltage	$\overline{\text{RESET}}$, CNVSS, BYTE, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1, VREF, XIN		–0.3 to V_{CC1}+0.3 (1)	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7		–0.3 to V_{CC2}+0.3 (1)	V
		P7_0, P7_1		–0.3 to 6.5	V
V_O	Output Voltage	P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1, XOUT		–0.3 to V_{CC1}+0.3 (1)	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7		–0.3 to V_{CC2}+0.3 (1)	V
		P7_0, P7_1		–0.3 to 6.5	V
P_d	Power Dissipation		–40°C<T_{opr}≤85°C	300	mW
T_{opr}	Operating Ambient Temperature	When the Microcomputer is Operating		–20 to 85 / –40 to 85	°C
		Flash Program Erase		0 to 60	
T_{stg}	Storage Temperature			–65 to 150	°C

NOTES:
1. There is no external connections for port P1_0 to P1_7, P4_4 to P4_7, P7_2 to P7_5 and P9_1 in 80-pin version.

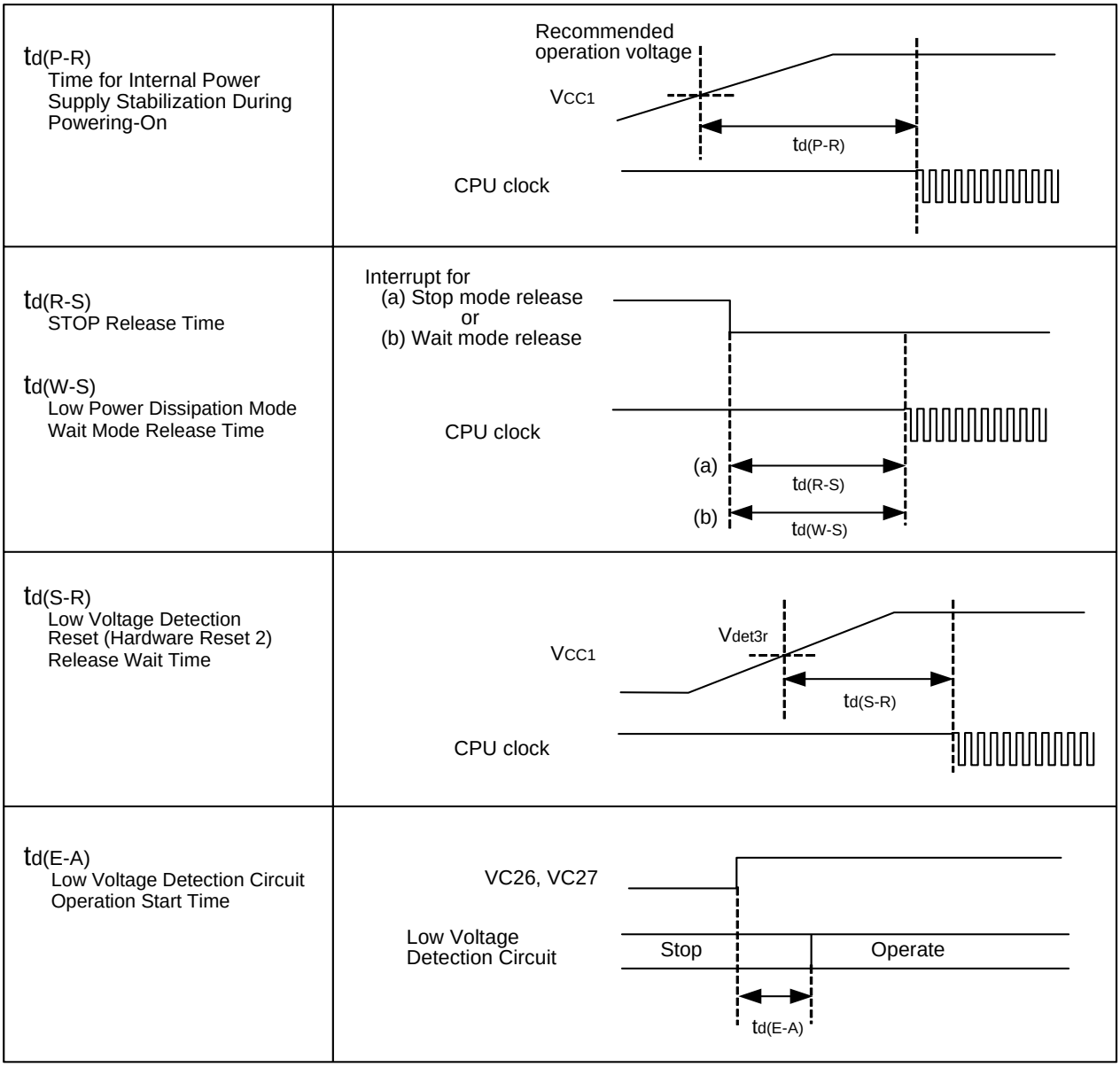


Figure 5.1 Power Supply Circuit Timing Diagram

Table 5.12 Electrical Characteristics (2) (1)

Symbol	Parameter		Measuring Condition		Standard			Unit
					Min.	Typ.	Max.	
I_{CC}	Power Supply Current (V_{CC1}=V_{CC2}=4.0V to 5.5V)	In single-chip mode, the output pins are open and other pins are V_{SS}	Mask ROM	f(BCLK)=24MHz No division, PLL operation		14	20	mA
				No division, On-chip oscillation		1		mA
			Flash Memory	f(BCLK)=24MHz, No division, PLL operation		18	27	mA
				No division, On-chip oscillation		1.8		mA
			Flash Memory Program	f(BCLK)=10MHz, VCC1=5.0V		15		mA
			Flash Memory Erase	f(BCLK)=10MHz, VCC1=5.0V		25		mA
			Mask ROM	f(XCIN)=32kHz Low power dissipation mode, ROM (3)		25		µA
			Flash Memory	f(BCLK)=32kHz Low power dissipation mode, RAM (3)		25		µA
				f(BCLK)=32kHz Low power dissipation mode, Flash Memory (3)		420		µA
				On-chip oscillation, Wait mode		50		µA
			Mask ROM Flash Memory	f(BCLK)=32kHz Wait mode (2), Oscillation capability High		7.5		µA
				f(BCLK)=32kHz Wait mode (2), Oscillation capability Low		2.0		µA
				Stop mode Topr =25°C		0.8	3.0	µA
I_{det4}	Low Voltage Detection Dissipation Current (4)					0.7	4	µA
I_{det3}	Reset Area Detection Dissipation Current (4)					1.2	8	µA

NOTES:
1. Referenced to V_{CC1}=V_{CC2}=4.2 to 5.5V, V_{SS} = 0V at T_{opr} = –20 to 85°C / –40 to 85°C, f(BCLK)=24MHz unless otherwise specified.
2. With one timer operated using fC32.
3. This indicates the memory in which the program to be executed exists.
4. I_{det} is dissipation current when the following bit is set to “1” (detection circuit enabled).

   I_{det4}: VC27 bit in the VCR2 register

   I_{det3}: VC26 bit in the VCR2 register

$V_{CC1}=V_{CC2}=5V$

Switching Characteristics

(V_{CC1} = V_{CC2} = 5V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.27 Memory Expansion and Microprocessor Modes (for setting with no wait)

Symbol	Parameter		Standard		Unit
			Min.	Max.	
td(BCLK-AD)	Address Output Delay Time	See **Figure 5.2**		25	ns
th(BCLK-AD)	Address Output Hold Time (in relation to BCLK)		4		ns
th(RD-AD)	Address Output Hold Time (in relation to RD)		0		ns
th(WR-AD)	Address Output Hold Time (in relation to WR)		(NOTE 2)		ns
td(BCLK-CS)	Chip Select Output Delay Time			25	ns
th(BCLK-CS)	Chip Select Output Hold Time (in relation to BCLK)		4		ns
td(BCLK-ALE)	ALE Signal Output Delay Time			15	ns
th(BCLK-ALE)	ALE Signal Output Hold Time		–4		ns
td(BCLK-RD)	RD Signal Output Delay Time			25	ns
th(BCLK-RD)	RD Signal Output Hold Time		0		ns
td(BCLK-WR)	WR Signal Output Delay Time			25	ns
th(BCLK-WR)	WR Signal Output Hold Time		0		ns
td(BCLK-DB)	Data Output Delay Time (in relation to BCLK)			40	ns
th(BCLK-DB)	Data Output Hold Time (in relation to BCLK) (3)		4		ns
td(DB-WR)	Data Output Delay Time (in relation to WR)		(NOTE 1)		ns
th(WR-DB)	Data Output Hold Time (in relation to WR) (3)		(NOTE 2)		ns
td(BCLK-HLDA)	HLDA Output Delay Time			40	ns

NOTES:

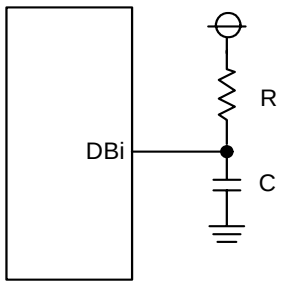
1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^{9}}{f(BCLK)} - 40[ns]$$ f(BCLK) is 12.5MHz or less.

2. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^{9}}{f(BCLK)} - 10[ns]$$

3. This standard value shows the timing when the output is off, and does not show hold time of data bus.
   Hold time of data bus varies with capacitor volume and pull-up (pull-down) resistance value.
   Hold time of data bus is expressed in
   $t = -CR \times \ln(1 - V_{OL} / V_{CC2})$
   by a circuit of the right figure.
   For example, when $V_{OL} = 0.2V_{CC2}$, C = 30pF, R = 1kΩ, hold time of output "L" level is
   $t = -30pF \times 1k\Omega \times \ln(1 - 0.2V_{CC2} / V_{CC2})$
   = 6.7ns.



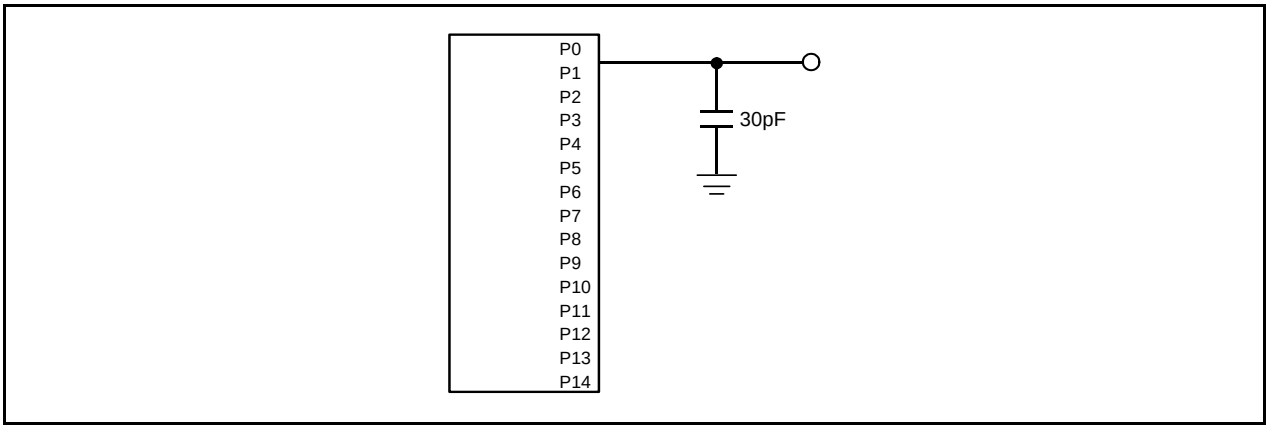


Figure 5.2 Ports P0 to P14 Measurement Circuit

$V_{CC1}=V_{CC2}=5V$

Switching Characteristics

(V_{CC1} = V_{CC2} = 5V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.29 Memory Expansion and Microprocessor Modes (for 2- to 3-wait setting, external area access and multiplex bus selection)

Symbol	Parameter		Standard		Unit
			Min.	Max.	
td(BCLK-AD)	Address Output Delay Time	See **Figure 5.2**		25	ns
th(BCLK-AD)	Address Output Hold Time (in relation to BCLK)		4		ns
th(RD-AD)	Address Output Hold Time (in relation to RD)		(NOTE 1)		ns
th(WR-AD)	Address Output Hold Time (in relation to WR)		(NOTE 1)		ns
td(BCLK-CS)	Chip Select Output Delay Time			25	ns
th(BCLK-CS)	Chip Select Output Hold Time (in relation to BCLK)		4		ns
th(RD-CS)	Chip Select Output Hold Time (in relation to RD)		(NOTE 1)		ns
th(WR-CS)	Chip Select Output Hold Time (in relation to WR)		(NOTE 1)		ns
td(BCLK-RD)	RD Signal Output Delay Time			25	ns
th(BCLK-RD)	RD Signal Output Hold Time		0		ns
td(BCLK-WR)	WR Signal Output Delay Time			25	ns
th(BCLK-WR)	WR Signal Output Hold Time		0		ns
td(BCLK-DB)	Data Output Delay Time (in relation to BCLK)			40	ns
th(BCLK-DB)	Data Output Hold Time (in relation to BCLK)		4		ns
td(DB-WR)	Data Output Delay Time (in relation to WR)		(NOTE 2)		ns
th(WR-DB)	Data Output Hold Time (in relation to WR)		(NOTE 1)		ns
td(BCLK-HLDA)	HLDA Output Delay Time			40	ns
td(BCLK-ALE)	ALE Signal Output Delay Time (in relation to BCLK)			15	ns
th(BCLK-ALE)	ALE Signal Output Hold Time (in relation to BCLK)		–4		ns
td(AD-ALE)	ALE Signal Output Delay Time (in relation to Address)		(NOTE 3)		ns
th(AD-ALE)	ALE Signal Output Hold Time (in relation to Address)		(NOTE 4)		ns
td(AD-RD)	RD Signal Output Delay From the End of Address		0		ns
td(AD-WR)	WR Signal Output Delay From the End of Address		0		ns
tdz(RD-AD)	Address Output Floating Start Time			8	ns

NOTES:

1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{f(BCLK)} - 10[ns]$$

2. Calculated according to the BCLK frequency as follows:

$$\frac{(n-0.5) \times 10^9}{f(BCLK)} - 40[ns]$$

n is “2” for 2-wait setting, “3” for 3-wait setting.

3. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{f(BCLK)} - 25[ns]$$

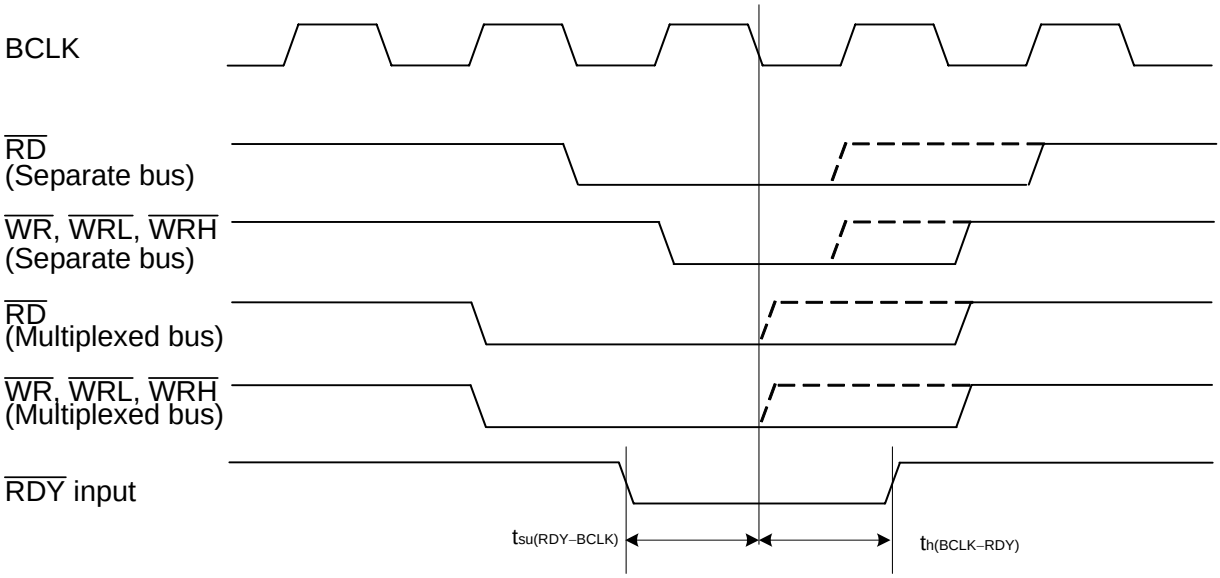
4. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{f(BCLK)} - 15[ns]$$

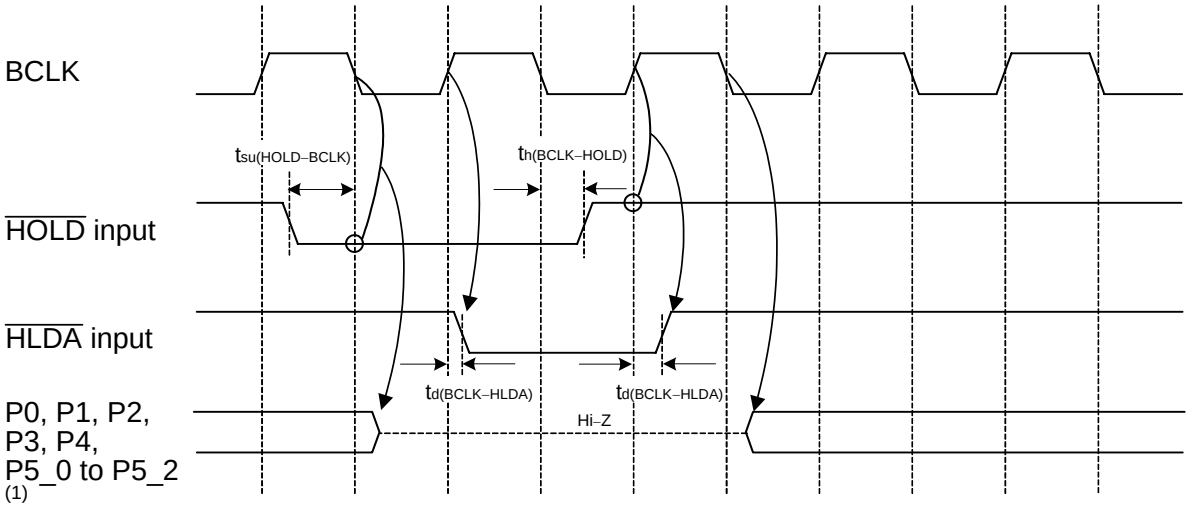
$V_{CC1}=V_{CC2}=5V$

Memory Expansion Mode, Microprocessor Mode

(Effective for setting with wait**)**



(Common to setting with wait and setting without wait**)**



NOTES:

1. These pins are set to high-impedance regardless of the input level of the BYTE pin, PM06 bit in PM0 register and PM11 bit in PM1 register.

· Measuring conditions :
· $V_{CC1}=V_{CC2}=5V$
· Input timing voltage : Determined with $V_{IL}=1.0V$, $V_{IH}=4.0V$
· Output timing voltage : Determined with $V_{OL}=2.5V$, $V_{OH}=2.5V$

Figure 5.5 Timing Diagram (3)

$V_{CC1}=V_{CC2}=3V$

Table 5.30 Electrical Characteristics (1) (1)

Symbol	Parameter		Measuring Condition	Standard			Unit
				Min.	Typ.	Max.	
V_{OH}	HIGH Output Voltage (3)	P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1	I_{OH}=–1mA	V_{CC1}–0.5		V_{CC1}	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	I_{OH}=–1mA (2)	V_{CC2}–0.5		V_{CC2}	
V_{OH}	HIGH Output Voltage XOUT	HIGHPOWER	I_{OH}=–0.1mA	V_{CC1}–0.5		V_{CC1}	V
		LOWPOWER	I_{OH}=–50µA	V_{CC1}–0.5		V_{CC1}	
	HIGH Output Voltage XCOUT	HIGHPOWER	With no load applied		2.5		V
		LOWPOWER	With no load applied		1.6		
V_{OL}	LOW Output Voltage (3)	P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1	I_{OL}=1mA			0.5	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	I_{OL}=1mA (2)			0.5	
V_{OL}	LOW Output Voltage XOUT	HIGHPOWER	I_{OL}=0.1mA			0.5	V
		LOWPOWER	I_{OL}=50µA			0.5	
	LOW Output Voltage XCOUT	HIGHPOWER	With no load applied		0		V
		LOWPOWER	With no load applied		0		
V_{T+}-V_{T-}	Hysteresis	$\overline{HOLD}$, $\overline{RDY}$, TA0IN to TA4IN, $\overline{TB0IN}$ to $\overline{TB5IN}$, $\overline{INT0}$ to $\overline{INT5}$, $\overline{NMI}$, $\overline{ADTRG}$, $\overline{CTS0}$ to $\overline{CTS2}$, CLK0 to CLK4, TA0OUT to TA4OUT, $\overline{KI0}$ to $\overline{KI3}$, RXD0 to RXD2, SCL0 to SCL2, SDA0 to SDA2, SIN3, SIN4		0.2		0.8	V
V_{T+}-V_{T-}	Hysteresis	$\overline{RESET}$		0.2	(0.7)	1.8	V
I_{IH}	HIGH Input Current (3)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1, XIN, $\overline{RESET}$, CNVSS, BYTE	V_I=3V			4.0	µA
I_{IL}	LOW Input Current (3)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1, XIN, $\overline{RESET}$, CNVSS, BYTE	V_I=0V			–4.0	µA
R_{PULLUP}	Pull-Up Resistance (3)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7,P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1	V_I=0V	50	100	500	kΩ
R_{fXIN}	Feedback Resistance XIN				3.0		MΩ
R_{fXCIN}	Feedback Resistance XCIN				25		MΩ
V_{RAM}	RAM Retention Voltage		At stop mode	2.0			V

NOTES:
1. Referenced to V_{CC1} = V_{CC2} = 2.7 to 3.3V, V_{SS} = 0V at Topr = –20 to 85°C / –40 to 85°C, f(XIN)=10MHz no wait unless otherwise specified.
2. V_{CC1} for the port P6 to P11 and P14, and V_{CC2} for the port P0 to P5 and P12 to P13
3. There is no external connections for port P1_0 to P1_7, P4_4 to P4_7, P7_2 to P7_5 and P9_1 in 80-pin version.

$V_{CC1}=V_{CC2}=3V$

Timing Requirements
(V_{CC1} = V_{CC2} = 3V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.34 Timer A Input (Counter Input in Event Counter Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TA)}$	TAiIN Input Cycle Time	150		ns
$t_{w(TAH)}$	TAiIN Input HIGH Pulse Width	60		ns
$t_{w(TAL)}$	TAiIN Input LOW Pulse Width	60		ns

Table 5.35 Timer A Input (Gating Input in Timer Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TA)}$	TAiIN Input Cycle Time	600		ns
$t_{w(TAH)}$	TAiIN Input HIGH Pulse Width	300		ns
$t_{w(TAL)}$	TAiIN Input LOW Pulse Width	300		ns

Table 5.36 Timer A Input (External Trigger Input in One-shot Timer Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TA)}$	TAiIN Input Cycle Time	300		ns
$t_{w(TAH)}$	TAiIN Input HIGH Pulse Width	150		ns
$t_{w(TAL)}$	TAiIN Input LOW Pulse Width	150		ns

Table 5.37 Timer A Input (External Trigger Input in Pulse Width Modulation Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(TAH)}$	TAiIN Input HIGH Pulse Width	150		ns
$t_{w(TAL)}$	TAiIN Input LOW Pulse Width	150		ns

Table 5.38 Timer A Input (Counter Increment/Decrement Input in Event Counter Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(UP)}$	TAiOUT Input Cycle Time	3000		ns
$t_{w(UPH)}$	TAiOUT Input HIGH Pulse Width	1500		ns
$t_{w(UPL)}$	TAiOUT Input LOW Pulse Width	1500		ns
$t_{su(UP-TIN)}$	TAiOUT Input Setup Time	600		ns
$t_{h(TIN-UP)}$	TAiOUT Input Hold Time	600		ns

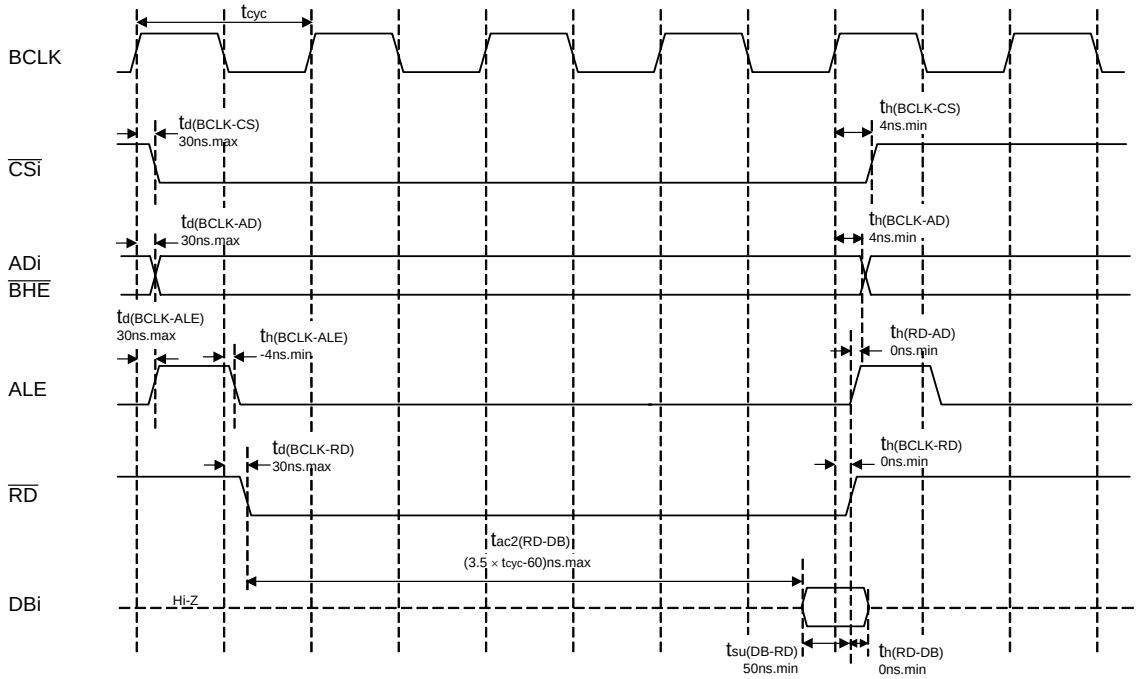
Table 5.39 Timer A Input (Two-phase Pulse Input in Event Counter Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TA)}$	TAiIN Input Cycle Time	2		µs
$t_{su(TAIN-TAOUT)}$	TAiOUT Input Setup Time	500		ns
$t_{su(TAOUT-TAIN)}$	TAiIN Input Setup Time	500		ns

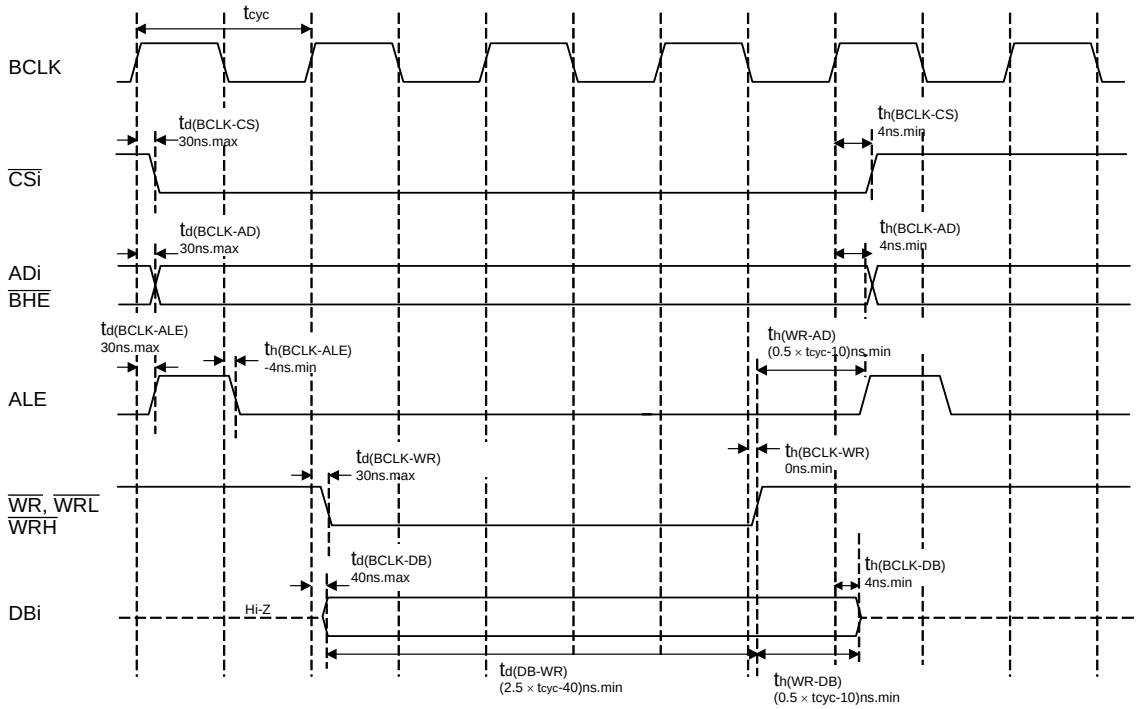
$V_{CC1} = V_{CC2} = 3V$

Memory Expansion Mode, Microprocessor Mode
(for 3-wait setting and external area access**)**

Read timing



Write timing



$$t_{cyc} = \frac{1}{f(BCLK)}$$

Measuring conditions
· V_{CC1}=V_{CC2}=3V
· Input timing voltage : V_{IL}=0.6V, V_{IH}=2.4V
· Output timing voltage : V_{OL}=1.5V, V_{OH}=1.5V

Figure 5.19 Timing Diagram (7)

Table 5.53 Flash Memory Version Electrical Characteristics (1) for 100 cycle products (B, U)

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance (3)		100			cycle
–	Word Program Time (V_{CC1}=5.0V)			25	200	µs
–	Lock Bit Program Time			25	200	µs
–	Block Erase Time (V_{CC1}=5.0V)	4-Kbyte block	4	0.3	4	s
–		8-Kbyte block		0.3	4	s
–		32-Kbyte block		0.5	4	s
–		64-Kbyte block		0.8	4	s
–	Erase All Unlocked Blocks Time (2)				4×n	s
t_{PS}	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time (5)		20			year

Table 5.54 Flash Memory Version Electrical Characteristics (6) for 10,000 cycle products (B7, U7) (Block A and Block 1 (7))

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance (3, 8, 9)		10,000 (4)			cycle
–	Word Program Time (V_{CC}1=5.0V)			25		µs
–	Lock Bit Program Time			25		µs
–	Block Erase Time (V_{CC1}=5.0V)	4-Kbyte block	4	0.3		s
t_{PS}	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time (5)		20			year

NOTES:
1. Referenced to V_{CC1}=4.5 to 5.5V at T_{opr} = 0 to 60 °C unless otherwise specified.
2. n denotes the number of block erases.
3. Program and Erase Endurance refers to the number of times a block erase can be performed.
   If the program and erase endurance is n (n=100, 1,000, or 10,000), each block can be erased n times.
   For example, if a 4 Kbytes block A is erased after writing 1 word data 2,048 times, each to a different address, this counts as one program and erase endurance. Data cannot be written to the same address more than once without erasing the block. (Rewrite prohibited)
4. Maximum number of E/W cycles for which operation is guaranteed.
5. Ta (ambient temperature)=55 °C. As to the data hold time except Ta=55 °C, please contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor.
6. Referenced to V_{CC1} = 4.5 to 5.5V at T_{opr} = –40 to 85 °C (B7, U7 (T version)) / –40 to 125 °C (B7, U7 (V version)) unless otherwise specified.
7. Table 5.54 applies for block A or block 1 program and erase endurance > 1,000. Otherwise, use Table 5.53.
8. To reduce the number of program and erase endurance when working with systems requiring numerous rewrites, write to unused word addresses within the block instead of rewrite. Erase block only after all possible addresses are used. For example, an 8-word program can be written 256 times maximum before erase becomes necessary.
   Maintaining an equal number of erasure between block A and block 1 will also improve efficiency. It is important to track the total number of times erasure is used.
9. Should erase error occur during block erase, attempt to execute clear status register command, then block erase command at least three times until erase error disappears.
10. Set the PM17 bit in the PM1 register to “1” (wait state) when executing more than 100 times rewrites (B7 and U7).
11. Customers desiring E/W failure rate information should contact their Renesas technical support representative.

Table 5.55 Flash Memory Version Program/Erase Voltage and Read Operation Voltage Characteristics (at T_{opr} = 0 to 60 °C(B, U), T_{opr} = –40 to 85 °C (B7, U7 (T version)) / –40 to 125 °C (B7, U7 (V version))

Flash Program, Erase Voltage	Flash Read Operation Voltage
V_{CC1} = 5.0 V ± 0.5 V	V_{CC1}=4.0 to 5.5 V

Table 5.58 Electrical Characteristics (2) (1)

Symbol	Parameter		Measuring Condition		Standard			Unit
					Min.	Typ.	Max.	
I_{CC}	Power Supply Current (V_{CC1}=V_{CC2}=4.0V to 5.5V)	In single-chip mode, the output pins are open and other pins are V_{SS}	Mask ROM	f(BCLK)=24MHz No division, PLL operation		14	20	mA
				No division, On-chip oscillation		1		mA
			Flash Memory	f(BCLK)=24MHz, No division, PLL operation		18	27	mA
				No division, On-chip oscillation		1.8		mA
			Flash Memory Program	f(BCLK)=10MHz, V_{CC1}=5.0V		15		mA
			Flash Memory Erase	f(BCLK)=10MHz, V_{CC1}=5.0V		25		mA
			Mask ROM	f(XCIN)=32kHz Low power dissipation mode, ROM (3)		25		µA
			Flash Memory	f(BCLK)=32kHz Low power dissipation mode, RAM (3)		25		µA
				f(BCLK)=32kHz Low power dissipation mode, Flash Memory (3)		420		µA
				On-chip oscillation, Wait mode		50		µA
			Mask ROM Flash Memory	f(BCLK)=32kHz Wait mode (2), Oscillation capability High		7.5		µA
				f(BCLK)=32kHz Wait mode (2), Oscillation capability Low		2.0		µA
				Stop mode Topr =25°C		2.0	6.0	µA
				Stop mode Topr =85°C			20	µA
				Stop mode Topr =125°C			TBD	µA

NOTES:
1. Referenced to V_{CC1}=V_{CC2}=4.0 to 5.5V, V_{SS} = 0V at T_{opr} = –40 to 85°C / –40 to 125°C, f(BCLK)=24MHz unless otherwise specified. T version = –40 to 85°C, V version =–40 to 125°C.
2. With one timer operated using fC32.
3. This indicates the memory in which the program to be executed exists.

$V_{CC1}=V_{CC2}=5V$

Timing Requirements
(V_{CC1} = V_{CC2} = 5V, V_{SS} = 0V, at T_{opr} = –40 to 85°C (T version) / –40 to 125°C (V version) unless otherwise specified)

Table 5.59 External Clock Input (XIN input)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
t_c	External Clock Input Cycle Time	62.5		ns
$t_{w(H)}$	External Clock Input HIGH Pulse Width	25		ns
$t_{w(L)}$	External Clock Input LOW Pulse Width	25		ns
t_r	External Clock Rise Time		15	ns
t_f	External Clock Fall Time		15	ns

$V_{CC1}=V_{CC2}=5V$

Switching Characteristics
(V_{CC1} = V_{CC2} = 5V, V_{SS} = 0V, at T_{opr} = –40 to 85°C (T version) / –40 to 125°C (V version) unless otherwise specified)

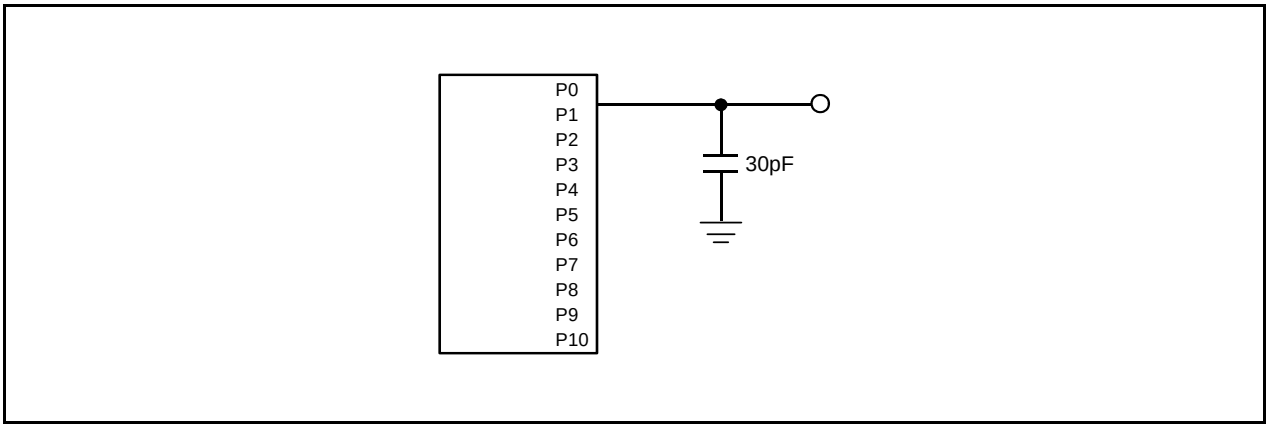
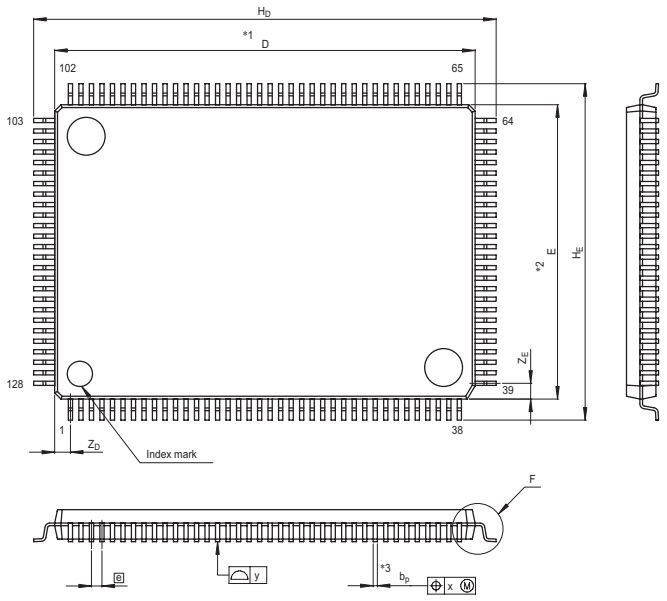
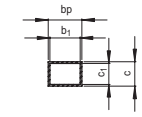


Figure 5.23 Ports P0 to P10 Measurement Circuit

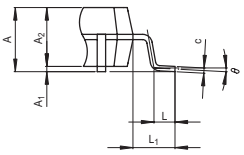
Appendix 1.Package Dimensions

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LQFP128-14x20-0.50	PLQP0128KB-A	128P6Q-A	0.9g





Terminal cross section

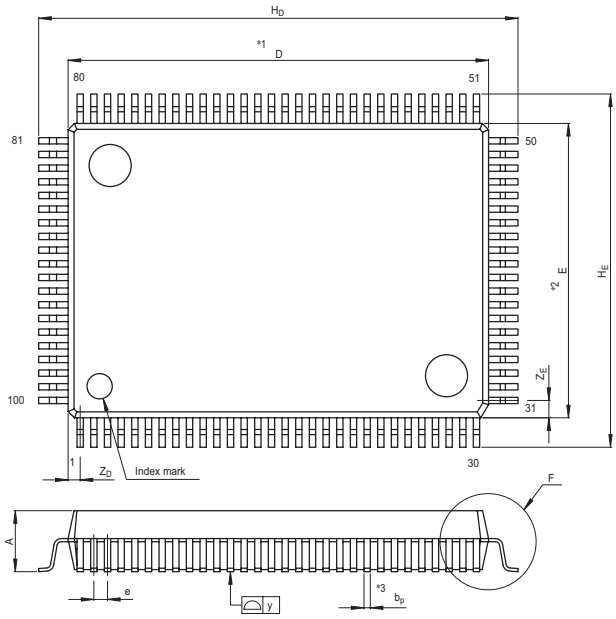


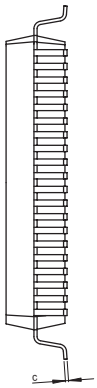
DetailF

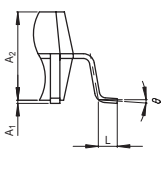
NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	19.9	20.0	20.1
E	13.9	14.0	14.1
A_2	—	1.4	—
H_D	21.8	22.0	22.2
H_E	15.8	16.0	16.2
A	—	—	1.7
A_1	0.05	0.125	0.2
b_p	0.17	0.22	0.27
b_1	—	0.20	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
e	—	0.5	—
x	—	—	0.10
y	—	—	0.10
Z_D	—	0.75	—
Z_E	—	0.75	—
L	0.35	0.5	0.65
L_1	—	1.0	—

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-QFP100-14x20-0.65	PRQP0100JB-A	100P6S-A	1.6g







Detail F

NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	19.8	20.0	20.2
E	13.8	14.0	14.2
A_2	—	2.8	—
H_D	22.5	22.8	23.1
H_E	16.5	16.8	17.1
A	—	—	3.05
A_1	0	0.1	0.2
b_p	0.25	0.3	0.4
c	0.13	0.15	0.2
θ	0°	—	10°
e	0.5	0.65	0.8
y	—	—	0.10
Z_D	—	0.575	—
Z_E	—	0.825	—
L	0.4	0.6	0.8

Rev.	Date	Description	
		Page	Summary
		33	Table 5.4 A-D Conversion Characteristics is revised.
			Table 5.5 D-A Conversion Characteristics revised.
		34,74	Table 5.6 to 5.7 and table 5.54 to 5.55 are revised.
		36	Table 5.11 is revised.
		38,55	Table 5.14 and 5.33 HLDA output deley time is deleted.
		41	Figure 5.1 is partly revised.
		41-43, 58-60	Table 5.27 to 5.29 and table 5.46 to 48 HLDA output deley time is added.
		44	Figure 5.2 Timing Diagram (1) XIN input is added.
		47-48	Figure 5.5 to 5.6 Read timing DB → DBi
		49-50	Figure 5.7 to 5.8 Write timing DB → DBi
		52	Figure 5.10 DB → DBi
		53	Table 5.30 is revised.
		58	Figure 5.11 is partly revised.
		61	Figure 5.12 Timing Diagram (1) XIN input is added.
		64-65	Figure 5.15 to 5.16 Read timing DB → DBi
		66-67	Figure 5.17 to 5.18 Write timing DB → DBi
		69	Figure 5.20 DB → DBi
		70-85	Electrical Characteristics (M16C/62PT) is added.
2.10	Nov 07, 2003	8-9	Table 1.5 to 1.7 Product List is partly revised. Note 1 is deleted.
		23	Table 3.1 is revised.
		71	Table 5.50 is revised.
		72	Table 5.51 is deleted.
2.11	Jan 06, 2004	16	Table 1.9 NOTE 3 VCC1 VCC2 → VCC1 > VCC2
		17-18	Table 1.10 to 1.11 NOTE 1 VCC1 VCC2 → VCC1 > VCC2
		31	Table 5.2 Power Supply Ripple Allowable Frequency Unit MHz → kHz
2.30	Sep 01, 2004	12	Table 1.9 and Figure 1.5 are added.
		18, 20	Table 1.11 to 1.13 are revised.
		19,21	Table 1.12 to 1.14 are revised.
		24	Figure 3.1 is partly revised.
			Note 3 is added.
		25	Note 6 is added.
		33	Table 5.3 is revised.
			Note 2 in Table 5.4 is added.
		34	Table 5.5 to 5.6 is partly revised.
		35	Table 5.8 is revised.
			Table 5.9 is revised.
		37	Table 5.11 is revised.